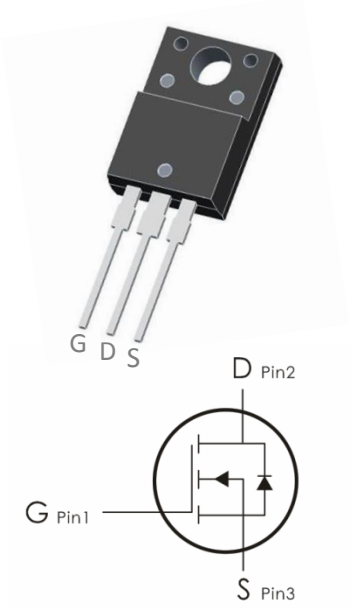
Description：

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.



Features：

1) V_{DS}=500V,I_D=5A,$R_{DS(ON)}$<1.4Ω @V_{GS}=10V
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity trench technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.

Absolute Maximum Ratings：(T_C=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Continuous Drain Current- T_C=25℃	5	A
	Continuous Drain Current-T_C=100℃	2.2	
E_{AS}	Single Pulse Avalanche Energy[1]	270	mJ
P_D	Power Dissipation	35	W
I_{AR}	valanche Current[2]	5	A
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case	3.45	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	110	

Electrical Characteristics: (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	500	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=500V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	2	---	4	V
$R_{DS(ON)}$	Drain-Source On Resistance	V_{GS}=10V,I_D=2.5A	---	---	1.4	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25, V_{GS}=0V, f=1MHz	---	800	1000	pF
C_{oss}	Output Capacitance		---	75	95	
C_{rss}	Reverse Transfer Capacitance		---	8.5	11	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=250v.I_D=5A R_{GEN}=25Ω. (Note3,4)	---	13	35	ns
t_r	Rise Time		---	55	120	ns
$t_{d(off)}$	Turn-Off Delay Time		---	25	60	ns
t_f	Fall Time		---	35	80	ns
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=400V I_D=5A. (Note3,4)	---	13	17	nC
Q_{gs}	Gate-Source Charge		---	3.4	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	6.4	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage	V_{GS}=0V,I_D=5A	---	---	1.5	V
Is	Max. Diode Forward Current	---	---	---	5	A
Ism	Max. Pulsed Forward Curent		---	---	20	A

Trr	Reverse Recovery Time	I_S=5A,V_{GS} =0V diF/dt=100A/μs (Note3)	---	215	---	Ns
qrr	Reverse Recovery Charge		---	1.26	---	nc

Notes : 1, L=27mH, IAS=5A, VDD=50V, RG=25Ω, Starting TJ =25°C
2, Repetitive Rating : Pulse width limited by maximum junction temperature
3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
4, Essentially Independent of Operating Temperature

Typical Characteristics: (T_C=25℃ unless otherwise noted)

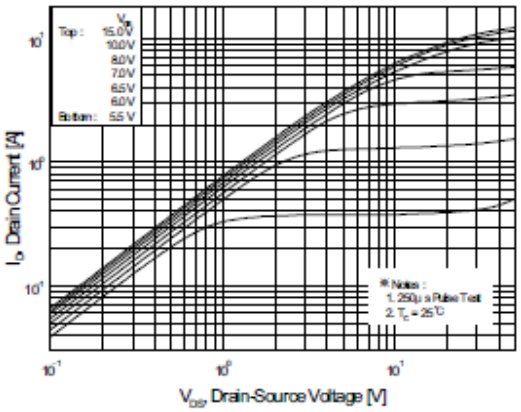


Figure 1. On-Region Characteristics

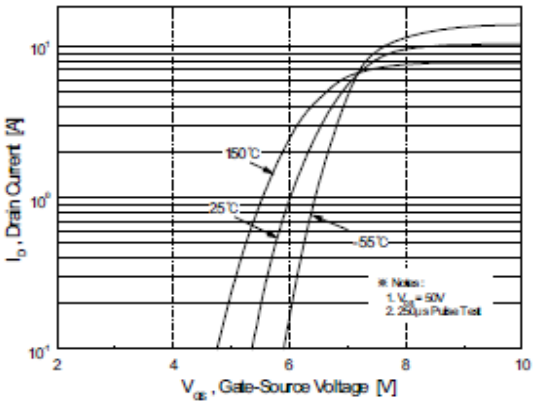


Figure 2. Transfer Characteristics

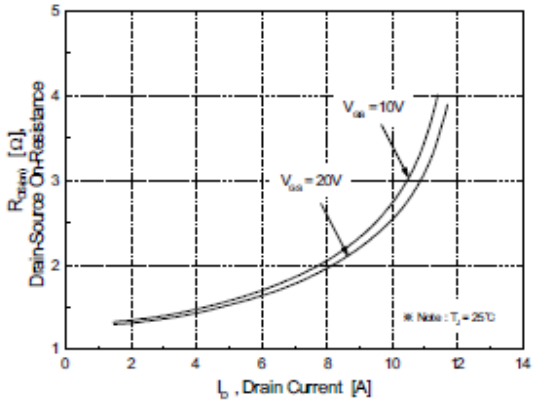


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

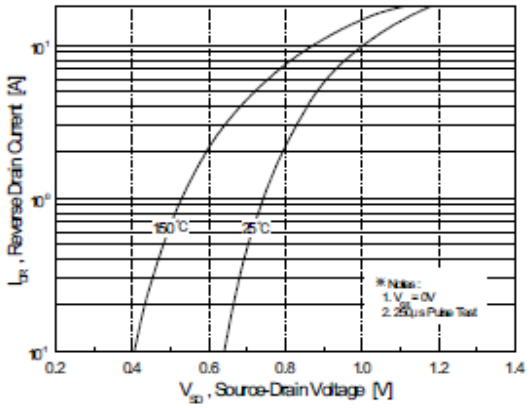


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

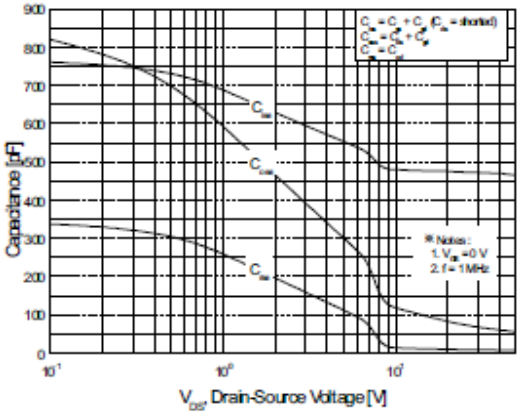


Figure 5. Capacitance Characteristics

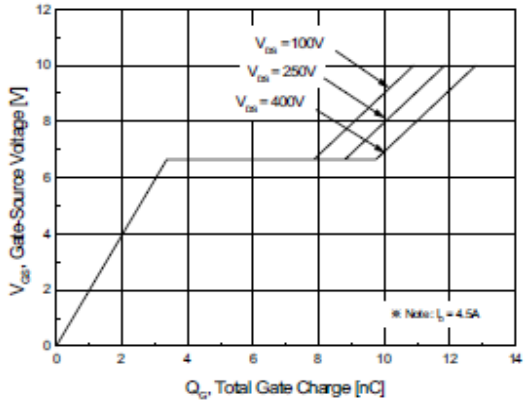


Figure 6. Gate Charge Characteristics

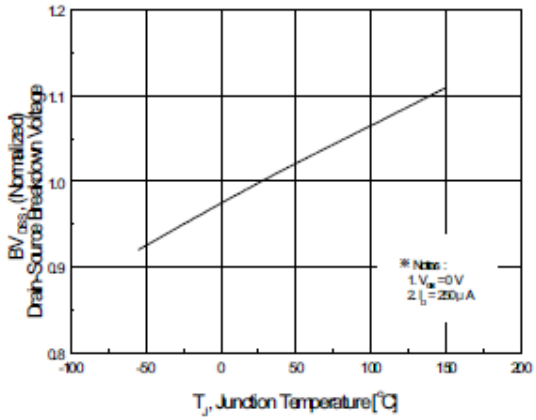


Figure 7. Breakdown Voltage Variation vs. Temperature

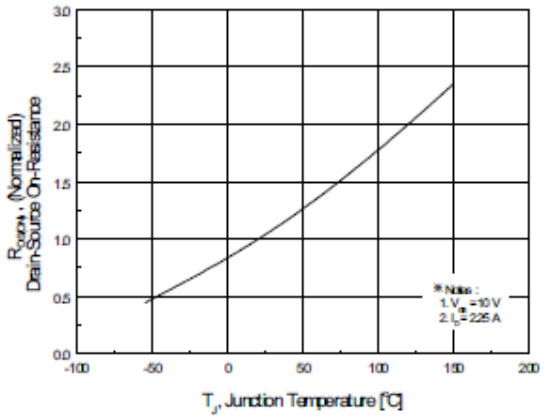


Figure 8. On-Resistance Variation vs. Temperature

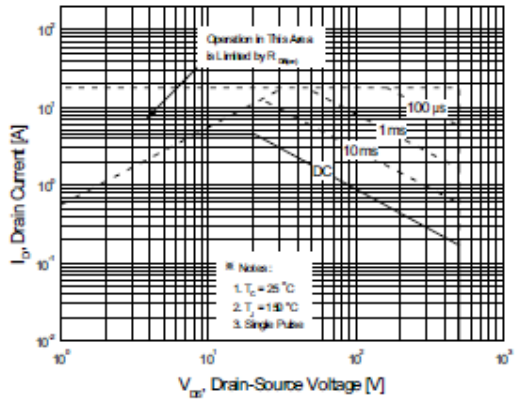


Figure 9. Maximum Safe Operating Area

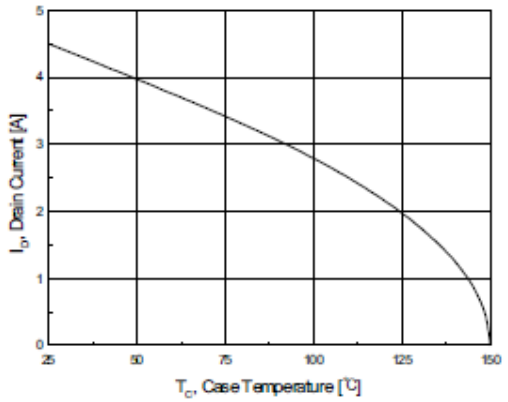


Figure 10. Maximum Drain Current vs. Case Temperature

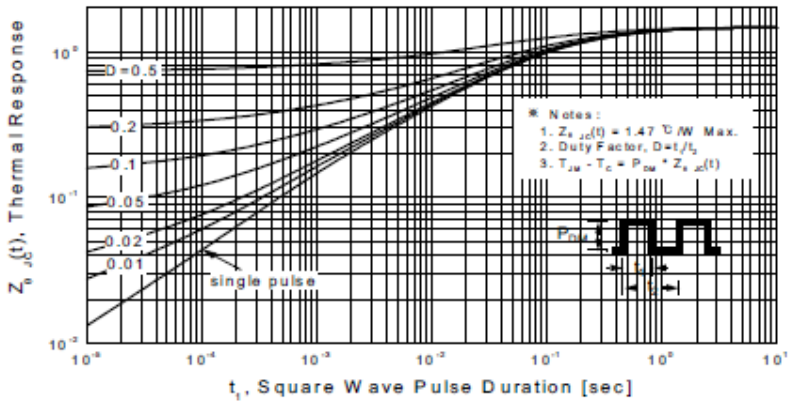


Figure 11. Transient Thermal Response Curve